2N6298 & 2N6299

PNP Darlington Power Silicon Transistor

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Available in JAN, JANTX, JANTXV per MIL-PRF-19500/540 TO-66 (TO-213AA) Package •

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Features

Ideal for High Gain Amplifier and Medium Speed Switching • Applications

Electrical Characteristics (T_A = +25°C unless otherwise noted)

Parameter	Test Conditions	Symbol	Units	Min.	Max.
Collector - Emitter Breakdown Voltage	I _C = -100 mA dc, 2N6298 I _C = -100 mA dc, 2N6299	V _{(BR)CEO}	V dc	-60 -80	_
Collector - Emitter Cutoff Current	V _{CE} = -30 V dc, 2N6298 V _{CE} = -40 V dc, 2N6299	I _{CEO}	mA dc	—	-0.5 -0.5
Collector - Emitter Cutoff Current	V_{CE} = -60 V dc, V_{BE} = +1.5 V dc, 2N6298 V_{CE} = -80 V dc, V_{BE} = +1.5 V dc, 2N6299	I _{CEX1}	µA dc	_	-10 -10
Emitter - Base Cutoff Current	V _{EB} = -5 V dc	I _{EBO}	mA dc	_	-2.0
Forward - Current Transfer Ratio	$V_{CE} = -3 V dc, I_C = -1 A dc$ $V_{CE} = -3 V dc, I_C = -4 A dc$ $V_{CE} = -3 V dc, I_C = -8 A dc$	h _{FE}	-	500 750 100	18,000
Collector - Emitter Saturation Voltage	$I_{C} = -4 \text{ A dc}, I_{B} = -16 \text{ mA dc}$ $I_{C} = -8 \text{ A dc}, I_{B} = -80 \text{ mA dc}$	V _{CE(sat)1} V _{CE(sat)2}	V dc	_	-2.0 -2.0
Base - Emitter Saturation Voltage	$I_{\rm C}$ = -8 A dc, $I_{\rm B}$ = -80 A dc	$V_{\text{BE(sat)}}$	V dc		-4.0
Base - Emitter Voltage	V_{CE} = -3 V dc, I _C = -4 A dc	$V_{\text{BE(on)}}$	V dc	_	-2.8
Collector - Emitter Cutoff Current	$T_{A} = +150^{\circ}C$ V _{CE} = -60 V dc, V _{BE} = +1.5 V dc, 2N6298 V _{CE} = -80 V dc, V _{BE} = +1.5 V dc, 2N6299	I _{CEX2}	mA dc	_	-5.0 -5.0
Forward - Current Transfer Ratio	$T_A = -55^{\circ}C$ V _{CE} = -3 V dc, I _C = -4 A dc	h _{FE4}	-	200	
Dynamic Characteristics					
Magnitude of Small-Signal Short-Circuit For- ward Current Transfer Ratio	V_{CE} = -3 V dc, I _C = -3 A dc, f = 1.0 MHz	h _{fe}	-	25	350
Small-Signal Short-Circuit Forward - Current Transfer Ratio	V _{CE} = -3 V dc, I _C = -3 A dc, f = 1.0 kHz	h _{fe}	-	300	_
Open Circuit Output Capacitance	V_{CB} = -10 V dc, I _E = 0, 100 kHz ≤ f ≤ 1 MHz	C _{obo}	pF	_	200
Switching Characteristics			· .		
Turn-On Time	V_{CC} = -30 V dc; I _C = -4 A dc; I _{B1} = -16 mA dc	t _{on}	μs	_	2.0
Turn-Off Time	V_{CC} = -30 Vdc; I _C = -4 A dc; I _{B1} = -16 mA dc	t _{off}	μs	_	8.0

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Rev. V5

PNP Darlington Power Silicon Transistor



Rev. V5

Absolute Maximum Ratings ($T_A = +25^{\circ}C$ unless otherwise noted)

Ratings	Symbol	Value
Collector - Emitter Voltage 2N6298 2N6299	V _{CEO}	-60 V dc -80 V dc
Collector - Base Voltage 2N6298 2N6299	V _{CBO}	-60 V dc -80 V dc
Emitter - Base Voltage	V_{EBO}	-5 V dc
Base Current	I _B	-120 mA dc
Collector Current	Ι _C	-8 A dc
Total Power Dissipation ⁽¹⁾ @ $T_C = +25^{\circ}C$ @ $T_C = +100^{\circ}C$	PT	64 W 32 W
Operating & Storage Temperature Range	T _J , T _{STG}	-65°C to +175°C

(1) Derate linearly at 0.428 W/°C above $T_C > +25^{\circ}C$.

Thermal Characteristics

Characteristics		Max. Value
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.33°C/W

Safe Operating Area	
DC Tests:	T_{C} = +25 °C + 10°C, I Cycle, t = 1.0 s
Test 1: Test 2: Test 3:	$V_{CE} = -8.0 \text{ V dc}, I_{C} = -8.0 \text{ A dc}$ $V_{CE} = -20 \text{ V dc}, I_{C} = -2.0 \text{ A dc}$ $V_{CE} = -60 \text{ V dc}, I_{C} = -100 \text{ mA dc}, 2N6298$ $V_{CE} = -80 \text{ V dc}, I_{C} = -100 \text{ mA dc}, 2N6299$

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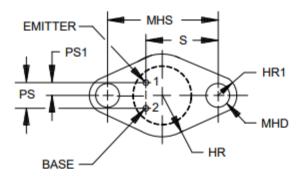
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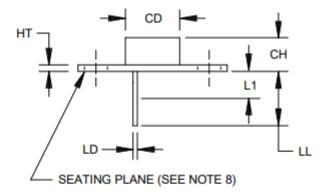
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Outline Drawing (TO-66)





	Dimensions				Symbol	Dimensions					
Symbol Inches		Millimeters		Notes		Inches		Millimeters		Notes	
	Min	Max	Min	Max			Min	Max	Min	Max	
CD		.620		15.75	3	LL	.360	.500	9.14	12.70	6
СН	.250	.340	6.35	8.64		L1		.050		1.27	6
HR		.350		8.89		MHD	.142	.152	3.61	3.86	4
HR1	.115	.145	2.92	3.68	4	MHS	.958	.962	24.33	24.43	
HT	.050	.075	1.27	1.91	5	PS	.190	.210	4.83	5.33	7
LD	.028	.034	0.71	0.86	4, 6	PS1	.093	.107	2.36	2.72	7
						S	.570	.590	14.48	14.99	

NOTES:

- 1. Dimensions are in inches. Millimeters are given for general information only.
- 2. Pin 1 is the emitter, pin 2 is the base. The collector shall be electrically connected to the case.
- Body contour is optional within zone defined by dimension CD.
- Two places.
- 5. Dimension HT does not include sealing flanges.
- Dimension LD applies between dimensions L1 and LL. Lead diameter shall not exceed twice dimension LD within dimension L1.
- These dimensions should be measured at points .050 inch (1.27 mm) +.005 inch (0.13 mm) to .000 inch (0.00 mm) below seating plane. When gauge is not used, measurement will be made at the seating plane.
- The seating plane of the header shall be flat within .001 inch (0.03 mm) concave to .004 inch (0.10 mm) convex inside a .930 inch (23.62 mm) diameter circle on the center of the header and flat within .001 inch (0.03 mm) concave to .006 inch (0.15 mm) convex overall.
- 9. In accordance with ASME Y14.5M, diameters are equivalent to Øx symbology.

FIGURE 1. Physical dimensions for diamond base flange mount TO-213AA (similar to TO-66) package.

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